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< High Voltage Insulated Gate Bipolar Transistor：HVIGBT >

CM1350HG-90X

HIGH POWER SWITCHING USE
INSULATED TYPE

5th-Version HVIGBT (High Voltage Insulated Gate Bipolar Transistor) Modules

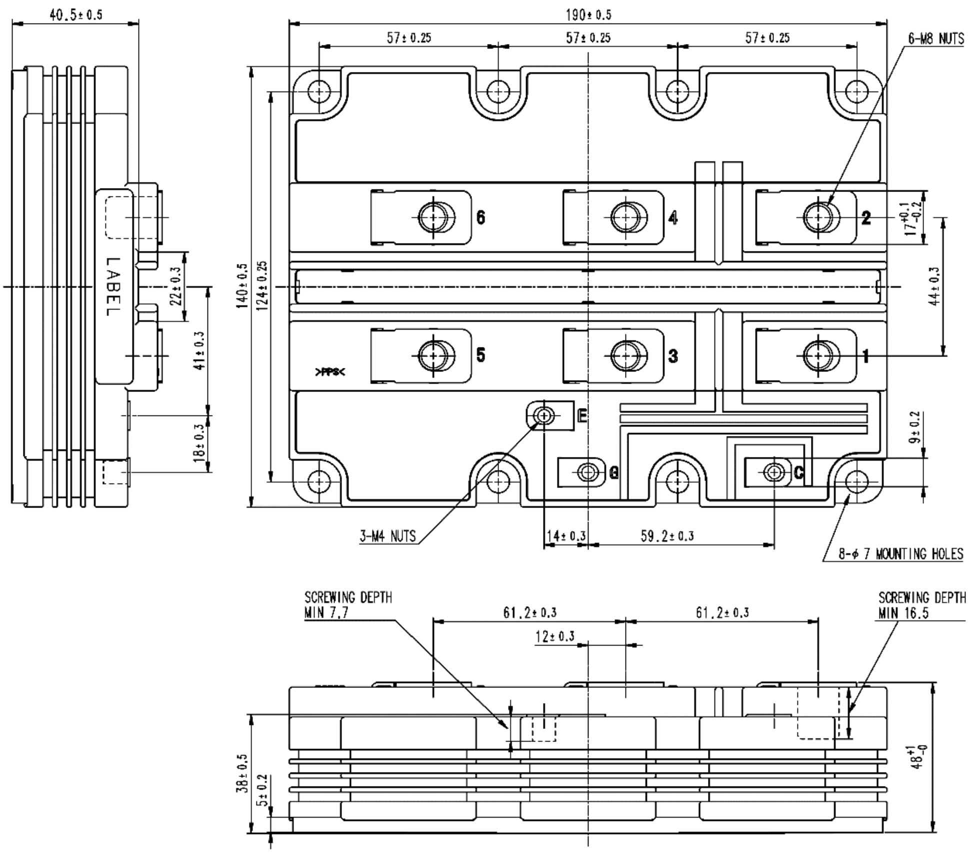
CM1350HG-90X

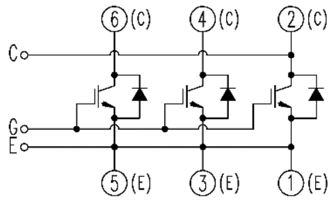
- I_C 1350A
- V_{CES} 4500V
- 1-element in a Pack
- Insulated Type
- CSTBT[TM](III) / RFC Diode
- AlSiC Baseplate
- UL recognized under UL1557

APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers

OUTLINE DRAWING & CIRCUIT DIAGRAM **Dimensions in mm**





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CIRCUIT DIAGRAM

Mar. 2019 (HVM-1075-J)

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MAXIMUM RATINGS

Symbol	Item	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	V_{GE} = 0V, T_j = -40…+150°C	4500	V
		V_{GE} = 0V, T_j = −50°C	4400	
V_{GES}	Gate-emitter voltage	V_{CE} = 0V, T_j = 25°C	± 20	V
I_C	Collector current	DC, T_C = 105°C	1350	A
I_{CRM}		Pulse (Note 1)	2700	A
I_E	Emitter current (Note 2)	DC	1350	A
I_{ERM}		Pulse (Note 1)	2700	A
P_{tot}	Maximum power dissipation (Note 3)	T_C = 25°C, IGBT part	14700	W
V_{iso}	Isolation voltage	RMS, sinusoidal, f = 60Hz, t = 1 min.	10200	V
V_e	Partial discharge extinction voltage	RMS, sinusoidal, f = 60Hz, Q_{PD} ≤ 10 pC	5100	V
T_j	Junction temperature		−50 ~ +150	°C
T_{jop}	Operating junction temperature		−50 ~ +150	°C
T_{stg}	Storage temperature		−55 ~ +150	°C
t_{psc}	Short circuit pulse width	V_{CC} = 3400V, V_{CE} ≤ V_{CES}, V_{GE} =15V, T_j =150°C	10	µs

ELECTRICAL CHARACTERISTICS

Symbol	Item	Conditions		Limits Min	Typ	Max	Unit
I_{CES}	Collector cutoff current	V_{CE} = V_{CES}, V_{GE} = 0V	T_j = 25°C	—	—	10.0	mA
			T_j = 125°C	—	10.0	—	
			T_j = 150°C	—	60.0	—	
$V_{GE(th)}$	Gate-emitter threshold voltage	V_{CE} = 10 V, I_C = 135 mA, T_j = 25°C		6.5	7.0	7.5	V
I_{GES}	Gate leakage current	V_{GE} = V_{GES}, V_{CE} = 0V, T_j = 25°C		−0.5	—	0.5	µA
C_{ies}	Input capacitance	V_{CE} = 10 V, V_{GE} = 0 V, f = 100 kHz, T_j = 25°C		—	170	—	nF
C_{oes}	Output capacitance			—	11.0	—	nF
C_{res}	Reverse transfer capacitance			—	1.5	—	nF
Q_G	Total gate charge	V_{CC} = 2800V, I_C = 1350A, V_{GE} = ±15V		—	12.6	—	µC
V_{CEsat}	Collector-emitter saturation voltage	I_C = 1350 A (Note 4), V_{GE} = 15 V	T_j = 25°C	—	2.25	—	V
			T_j = 125°C	—	2.90	—	
			T_j = 150°C	—	3.00	3.50	
$t_{d(on)}$	Turn-on delay time	V_{CC} = 2800 V, I_C = 1350 A, V_{GE} = ±15 V, $R_{G(on)}$ =2.4 Ω, L_s = 150 nH, Inductive load	T_j = 25°C	—	—	—	µs
			T_j = 125°C	—	0.55	—	
			T_j = 150°C	—	0.55	1.00	
t_r	Rise time		T_j = 25°C	—	—	—	µs
			T_j = 125°C	—	0.25	—	
			T_j = 150°C	—	0.25	0.50	
$E_{on(10\%)}$	Turn-on switching energy per pulse (Note 5)		T_j = 25°C	—	5.85	—	J
			T_j = 125°C	—	6.25	—	
			T_j = 150°C	—	6.30	—	
E_{on}	Turn-on switching energy per pulse (Note 6)		T_j = 25°C	—	5.95	—	J
			T_j = 125°C	—	6.60	—	
			T_j = 150°C	—	6.65	—	
$t_{d(off)}$	Turn-off delay time	V_{CC} = 2800 V, I_C = 1350 A, V_{GE} = ±15 V, $R_{G(off)}$ = 30 Ω, L_s = 150 nH, Inductive load	T_j = 25°C	—	—	—	µs
			T_j = 125°C	—	7.00	—	
			T_j = 150°C	—	7.20	10.0	
t_f	Fall time		T_j = 25°C	—	—	—	µs
			T_j = 125°C	—	0.50	—	
			T_j = 150°C	—	0.50	1.20	
$E_{off(10\%)}$	Turn-off switching energy per pulse (Note 5)		T_j = 25°C	—	3.90	—	J
			T_j = 125°C	—	5.30	—	
			T_j = 150°C	—	5.60	—	
E_{off}	Turn-off switching energy per pulse (Note 6)		T_j = 25°C	—	4.35	—	J
			T_j = 125°C	—	5.95	—	
			T_j = 150°C	—	6.25	—	

ELECTRICAL CHARACTERISTICS (continuation)

Symbol	Item	Conditions		Limits Min	Typ	Max	Unit
V_{EC}	Emitter-collector voltage (Note 2)	I_E = 1350 A (Note 4) V_{GE} = 0 V	T_j = 25°C	—	2.35	—	V
			T_j = 125°C	—	2.90	—	
			T_j = 150°C	—	3.00	3.50	
t_{rr}	Reverse recovery time (Note 2)	V_{CC} = 2800 V, I_C = 1350 A, V_{GE} = ±15 V, $R_{G(on)}$ = 2.4 Ω, L_s = 150 nH, Inductive load	T_j = 25°C	—	—	—	μs
			T_j = 125°C	—	1.45	—	
			T_j = 150°C	—	1.70	—	
I_{rr}	Reverse recovery current (Note 2)		T_j = 25°C	—	—	—	A
			T_j = 125°C	—	1900	—	
			T_j = 150°C	—	1900	—	
$Q_{rr(10\%)}$	Reverse recovery charge (Note 2,7)		T_j = 25°C	—	—	—	μC
			T_j = 125°C	—	2450	—	
			T_j = 150°C	—	2500	—	
Q_{rr}	Reverse recovery charge (Note 2,6)		T_j = 25°C	—	—	—	μC
			T_j = 125°C	—	2560	—	
			T_j = 150°C	—	2600	—	
$E_{rec(10\%)}$	Reverse recovery energy per pulse (Note 2,5)		T_j = 25°C	—	3.05	—	J
			T_j = 125°C	—	3.90	—	
			T_j = 150°C	—	4.00	—	
E_{rec}	Reverse recovery energy per pulse (Note 2,6)		T_j = 25°C	—	3.10	—	J
			T_j = 125°C	—	4.20	—	
			T_j = 150°C	—	4.30	—	

THERMAL CHARACTERISTICS

Symbol	Item	Conditions	Limits Min	Typ	Max	Unit
$R_{th(j-c)Q}$	Thermal resistance	Junction to Case, IGBT part	—	—	8.5	K/kW
$R_{th(j-c)D}$		Junction to Case, FWDi part	—	—	13.0	K/kW
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink λ_{grease} = 1W/m･k, $D_{(c-s)}$ = 80μm	—	5.0	—	K/kW

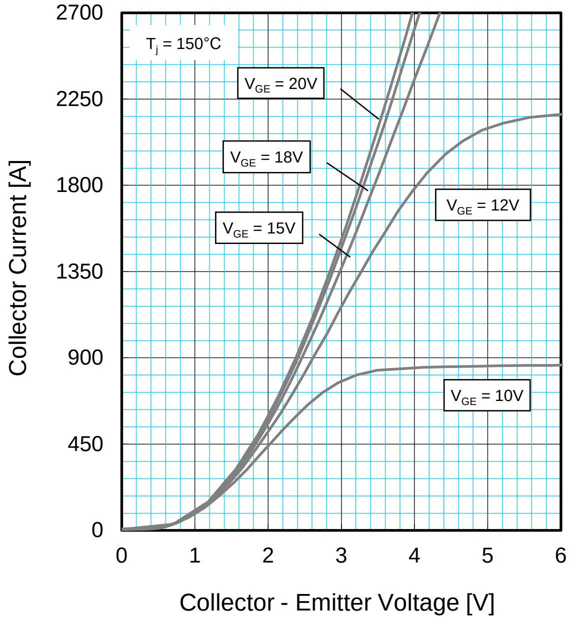
MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits Min	Typ	Max	Unit
M_t	Mounting torque	M8 : Main terminals screw	7.0	—	19.0	N·m
M_s		M6 : Mounting screw	3.0	—	6.0	N·m
M_t		M4 : Auxiliary terminals screw	1.0	—	3.0	N·m
m	Mass		—	1.5	—	kg
CTI	Comparative tracking index		600	—	—	—
d_a	Clearance		26.0	—	—	mm
d_s	Creepage distance		56.0	—	—	mm
$L_{P\ CE}$	Parasitic stray inductance		—	13.5	—	nH
$R_{CC'+EE'}$	Internal lead resistance	T_C = 25 °C	—	0.12	—	mΩ

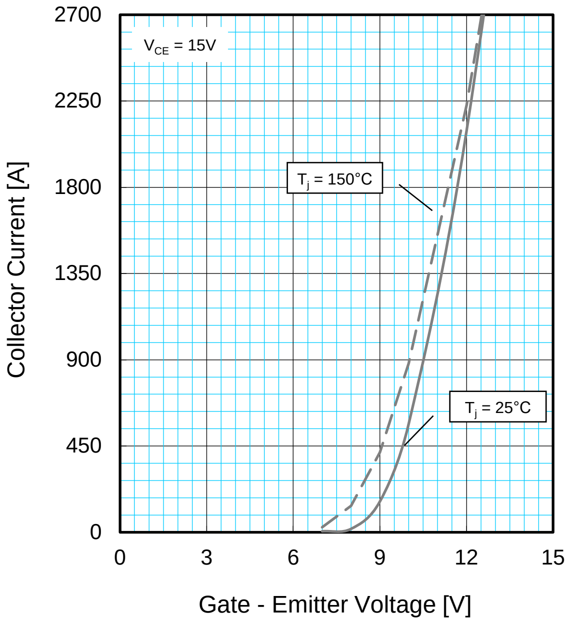
Note1. Pulse width and repetition rate should be such that junction temperature (T_j) does not exceed T_{jopmax} rating.
Note2. The symbols represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWD_i).
Note3. Junction temperature (T_j) should not exceed T_{jmax} rating (150°C).
Note4. Pulse width and repetition rate should be such as to cause negligible temperature rise.
Note5. The integration range of switching energies is from 10%V_{CE} to 10%I_C(10%I_E).
Note6. Definition of all items is according to IEC 60747, unless otherwise specified.
Note7. The integration range of reverse recovery charge is from I_E = 0A to 10%I_E.

PERFORMANCE CURVES

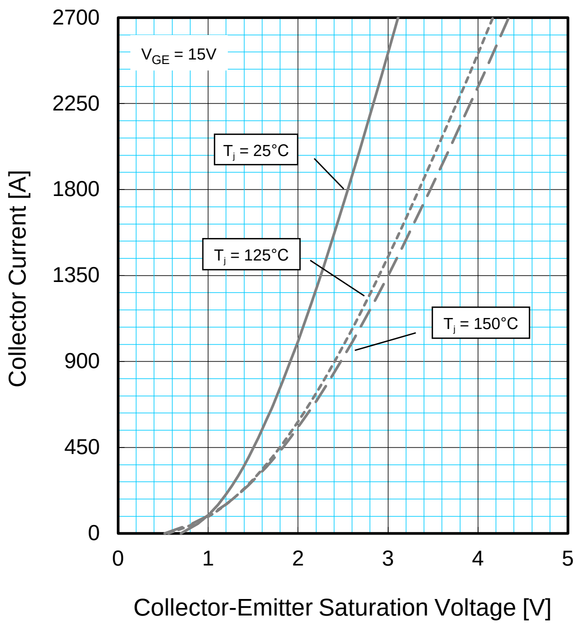
OUTPUT CHARACTERISTICS (TYPICAL)



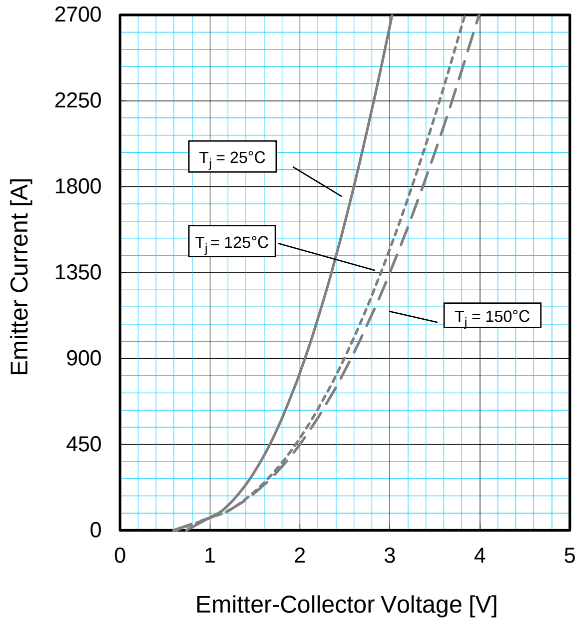
TRANSFER CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)

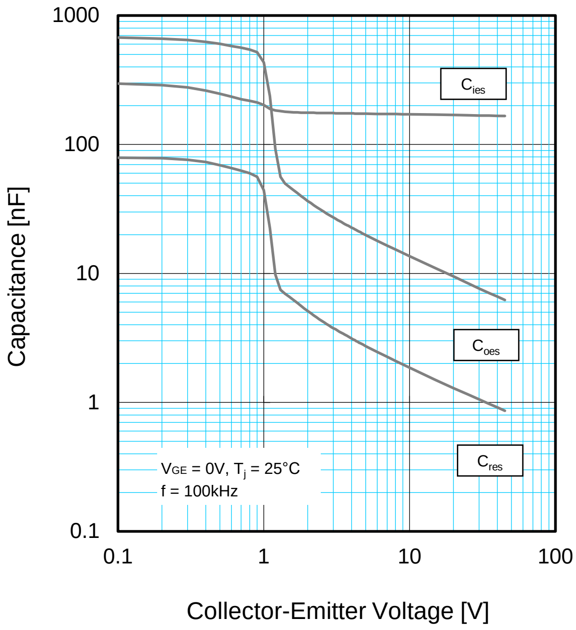


FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)

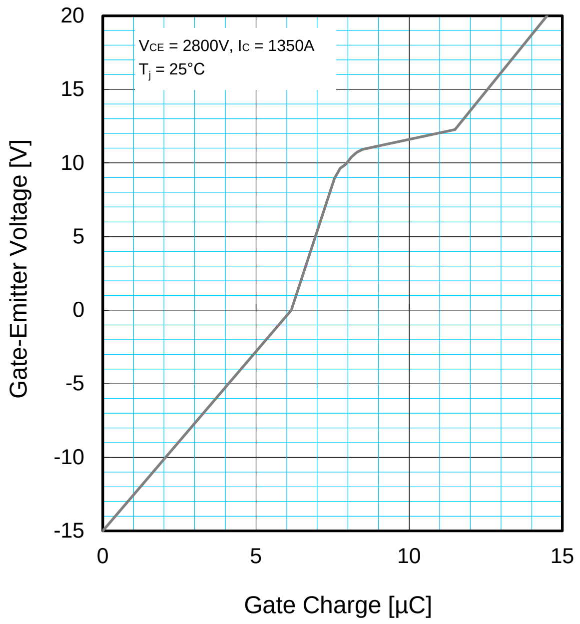


PERFORMANCE CURVES

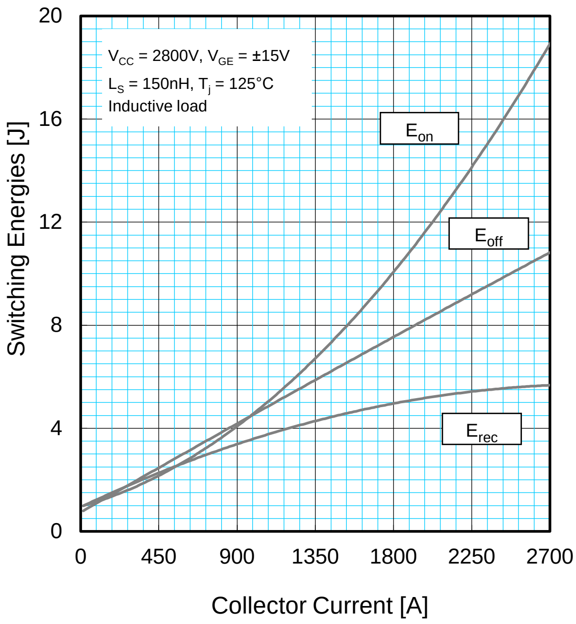
CAPACITANCE CHARACTERISTICS (TYPICAL)



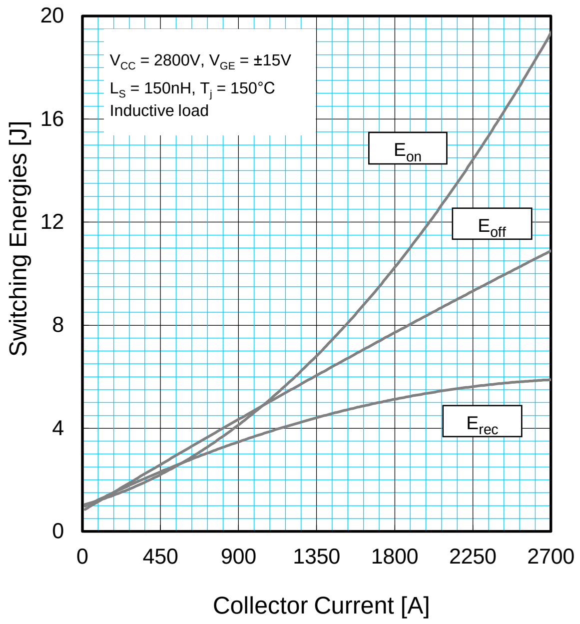
GATE CHARGE CHARACTERISTICS (TYPICAL)



HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)

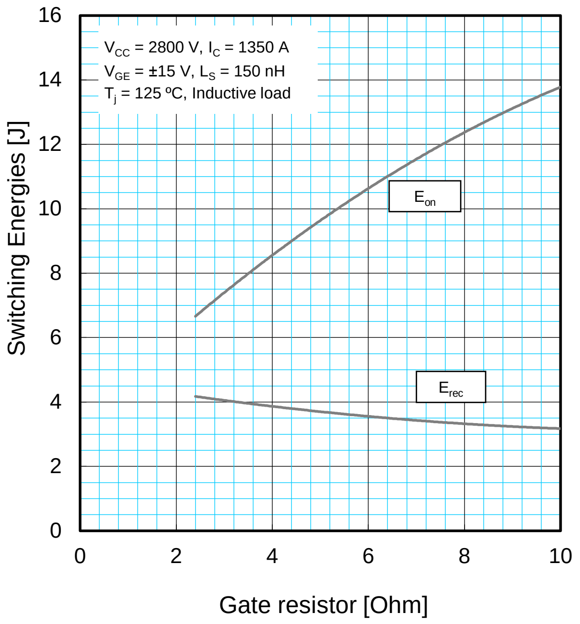


HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)



PERFORMANCE CURVES

HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)



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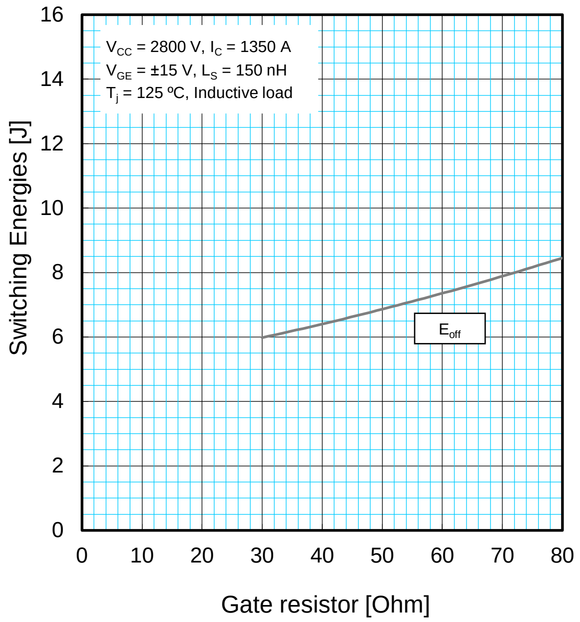

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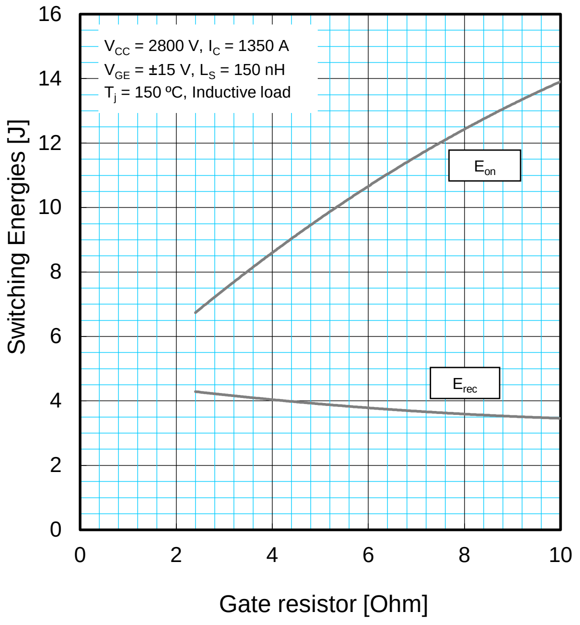
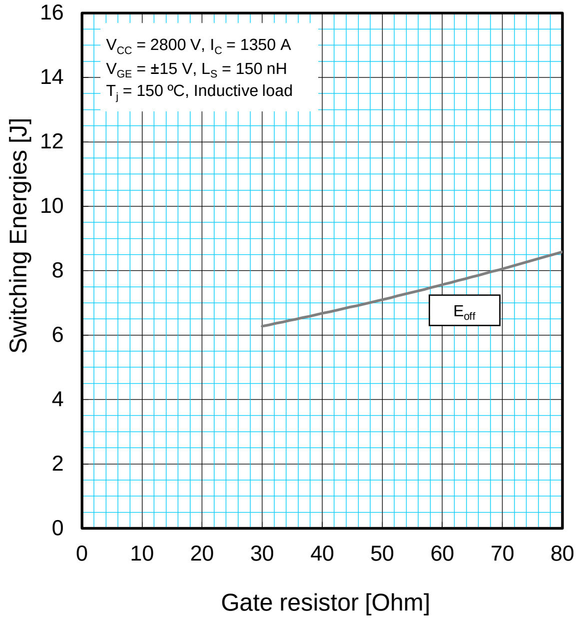
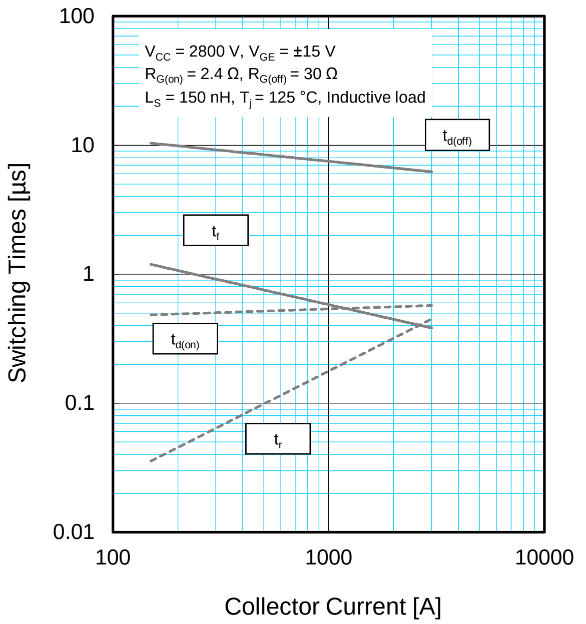


HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)

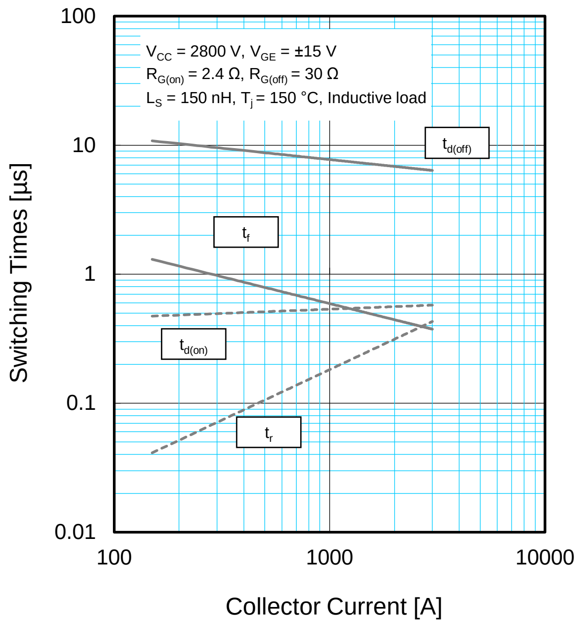


PERFORMANCE CURVES

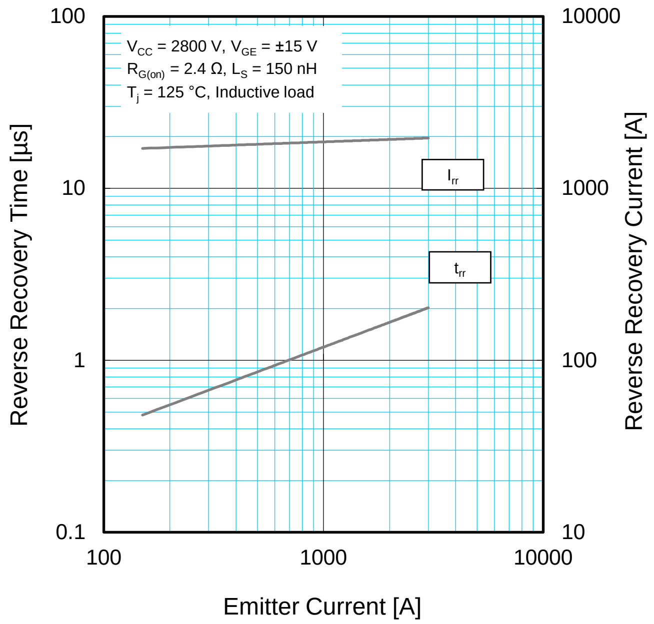
HALF-BRIDGE SWITCHING TIME CHARACTERISTICS (TYPICAL)



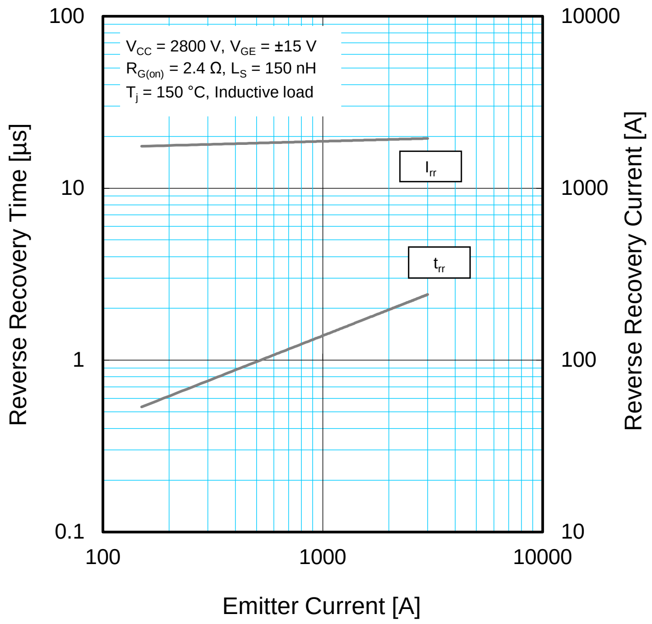
HALF-BRIDGE SWITCHING TIME CHARACTERISTICS (TYPICAL)



FREE-WHEEL DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

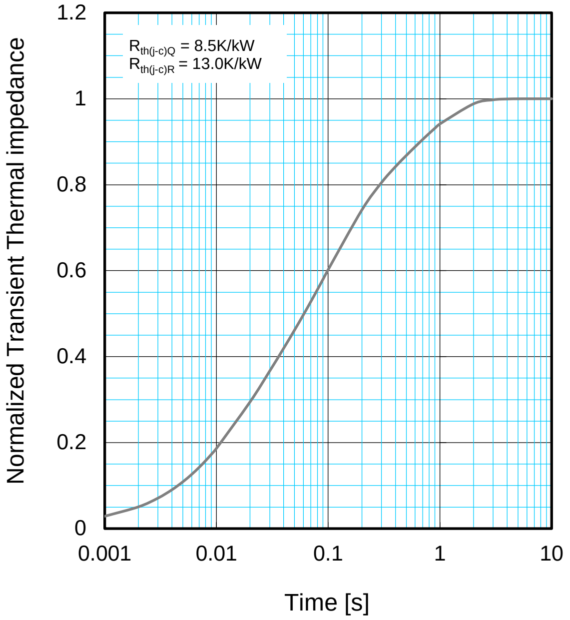


FREE-WHEEL DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



PERFORMANCE CURVES

TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

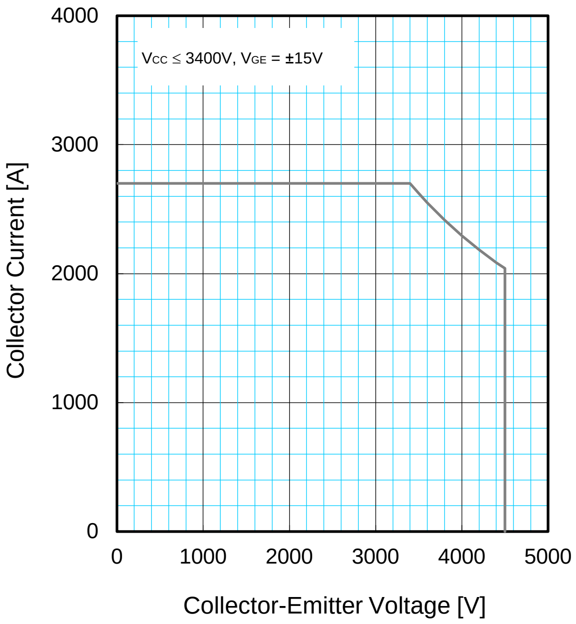


$$Z_{th(j-c)}(t)=\sum_{i=1}^{n}R_i\left\{1-\exp\left(-\frac{t}{\tau_i}\right)\right\}$$

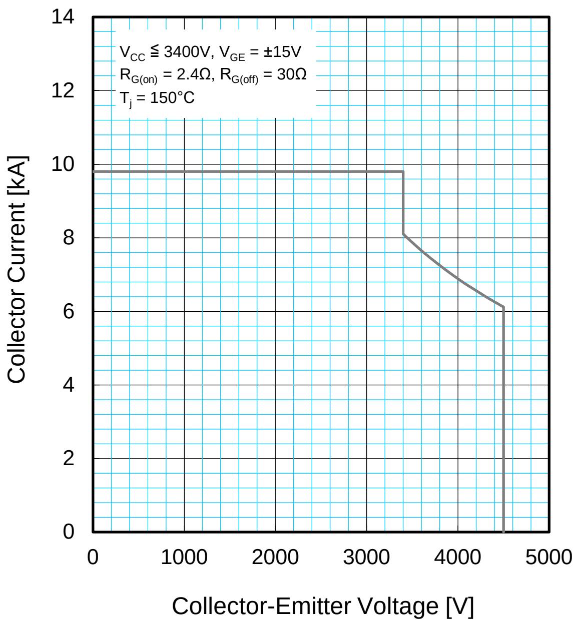
	1	2	3	4
R_i / $R_{th(j-c)}$:	0.0096	0.1893	0.4044	0.3967
τ_i [sec] :	0.0001	0.0058	0.0602	0.3512

PERFORMANCE CURVES

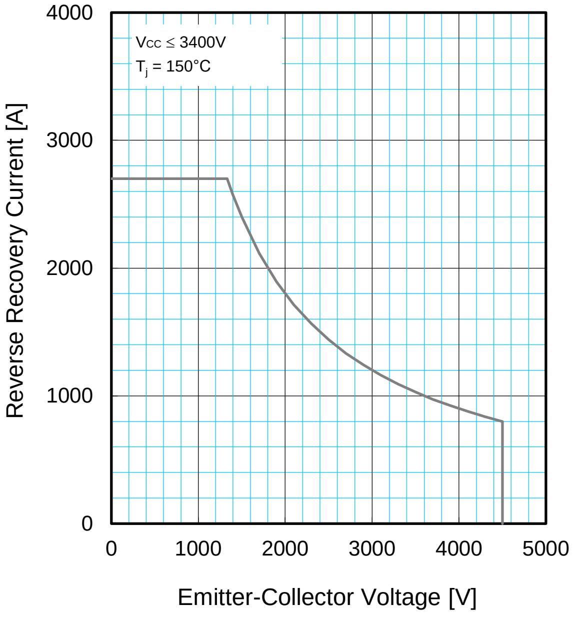
REVERSE BIAS SAFE OPERATING AREA (RBSOA)



SHORT CIRCUIT SAFE OPERATING AREA (SCSOA)



FREE-WHEEL DIODE REVERSE RECOVERY SAFE OPERATING AREA (RRSOA)



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